

PATENT

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**REVOCATION OF POWER OF ATTORNEY,  
NEW POWER OF ATTORNEY BY ASSIGNEE AND  
CHANGE OF CORRESPONDENCE ADDRESS**

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

**Customer No. 20792**

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

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Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patent application identified to Hewlett-Packard Development Company, L.P. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By: Jeong-Taek Kong  
Jeong-Taek Kong

Title: Senior Vice President of IP Team

Date: Aug. 23, 2007

# APPENDIX A

In re:	Serial No.:	Filed	Title:	Assignment Recorded:	Reel:	Frame:	Atty. Dkt. No.
Adelmann	10/621,632	07/17/03	Assisted Memory Device with Integrated Cache	HPDC 11/18/03 Samsung 07/26/07	014138 019613	0051 0170	5649-2218
Smith	10/743,662	12/22/03	MRAM with Controller	HPDC 12/22/03	014841	0615	5649-2219
Perner	11/252,143	10/17/05	System and Method for Reading a Memory Cell	Samsung 07/26/07 HPDC 01/27/04 Samsung 07/26/07	019611 014930 019612	0239 0571 0436	5649-2220
Anthony	11/021,268	12/23/04	Magnetic Memory Device and Methods for Making Same	HPC 02/10/03 HPDC 06/18/03	013737 013776	0985 0928	5649-2221
Jedwab	10/722,918	11/26/03	Magnetic Memory which Compares Compressed Fault Maps	Samsung 07/26/07 HPDC 11/26/03	019611 014756	0807 0631	5649-2222
Sesek	10/700,203	11/03/03	Magnetic Memory	Samsung 07/26/07 HPDC 06/22/04	019612 014764	0632 0438	5649-2223
Pline	10/725,855	12/02/03	Data Storage System with Error Correction Code and Replaceable Defective Memory	Samsung 07/26/07 HPDC 12/2/03	019611 014757	0690 0280	5649-2224
Spencer	11/203,755	8/15/05	Method of Packaging Magnetic Memory	HPC 03/04/03 HPDC 09/30/03	013801 014061	0643 0492	5649-2225
Lee	10/698,501	10/31/03	Heating MRAM Cells to Ease State Switching	Samsung 07/26/07 HPDC 02/09/04	019611 014320	0853 0883	5649-2226
Stobbs	10/631,404	07/30/03	Magnetic Shielding for Magnetic Random Access Memory	Samsung 07/26/07 HPDC 09/11/03	019613 013991	0864 0927	5649-2227
Taussig	10/914,255	08/09/04	Silver Island Anti-Fuse	HPDC 08/09/04	015678	0022	5649-2228
Sharma	10/414,927	04/16/03	Optical Signal Transmission Transducer	Samsung 07/26/07 HPC 06/09/03 HPDC 09/30/03	019613 013719 014061	0107 0101 0492	5649-2230
Perner	11/264,539	11/01/05	Controllably Connectable Strings of MRAM Cells	Samsung 07/26/07 HPDC 11/01/05	019612 017180	0029 0326	5649-2231
Nickel	10/315,748	12/10/02	Thermally-Assisted Switching of Magnetic Memory Elements	HPC 06/22/01 HPDC 06/18/03	011938 013776	0028 0928	5649-2232
Lee	10/692,612	10/24/03	A Method of Making a Magnetic Tunnel Junction Device	Samsung 07/26/07 HPDC 03/31/04	019614 014478	0059 0694	5649-2233
Nauka	10/698,717	10/31/03	Data Storage Device Including Conductive Probe and Ferroelectric Storage Medium	Samsung 07/26/07 HPDC 10/31/03	019612 014655	0095 0885	5649-2234
Perner et al.	10/698,896	10/31/03	Multi-Sample Read Circuit Having Test Mode of Operation	HPDC 03/25/04 Samsung 07/26/07	014461 019612	0725 0139	5649-2235
Nickel	10/733,089	12/11/03	Using Sense Lines to Thermally Control the State of an MRAM	HPDC 12/11/03 Samsung 07/26/07	014817 019613	0794 0913	5649-2236

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In re:	Serial No.	Filed	Title	Assignment Recorded:	Reel:	Frame:	Att. Dkt. No.
Nickel	10/934,922	09/02/04	Thin Film Device and a Method of Formation Thereof	HPDC 09/02/04 Samsung 07/26/07	015771 019612	0250 0922	5649-2237
Perner	10/934,243	09/03/04	Method and Apparatus for Multi-Plane MRAM	HPDC 09/03/04 Samsung 07/26/07	015774 019613	0570 0064	5649-2238
Zhang	10/721,574	11/25/03	Molecular Optoelectronic Memory Device	HPDC 03/31/04 Samsung 07/26/07	014478 019612	0530 0206	5649-2239
Sharma	11/285,991	11/23/05	Multi-Layered Magnetic Memory Structures	HPDC 11/23/05 Samsung 07/26/07	017281 019613	0685 0412	5649-2240
Sharma	11/118,828	04/29/05	Process for Forming Magnetic Memory Structures	HPDC 04/29/05 Samsung 07/26/07	016527 019611	0690 0287	5649-2241
Sharma	11/286,245	11/23/05	Multi-Layered Magnetic Memory Structures	HPDC 11/23/05 Samsung 07/26/07	017281 019613	0810 0465	5649-2242
Sharma et al.	11/286,009	11/23/05	Multi-Layered Magnetic Memory Structures	HPDC 11/23/05 Samsung 07/26/07	017281 019613	0828 0343	5649-2243
Perner	11/266,861	11/03/05	Analog Preamplifier Calibration	HPDC 11/03/05 Samsung 07/26/07	017195 019611	0971 0576	5649-2244
Perner	11/267,705	11/03/05	Digital Current Source	HPDC 11/03/05 Samsung 07/26/07	017226 019612	0959 0261	5649-2245
Nickel	11/050,273	02/03/05	Method of Fabricating a Manganese Diffusion Barrier	HPDC 06/06/06 Samsung 07/26/07	016306 019612	0539 0337	5649-2247
Eaton	10/661,448	09/11/03	Increased Magnetic Memory Array Sizes and Operating Margins	HPDC 12/03/03 Samsung 07/26/07	014171 019613	0302 0624	5649-2248
Sharma	10/831,110	04/26/04	Data Input Device That Utilizes A Layer Of Magnetic Particles To Store Non-Volatile Input Data That Is Magnetically Coupled To An Underlying MRAM Array (As Amended)	HPDC 04/26/04 Samsung 07/26/07	015226 019613	0350 0531	5649-2249
Nickel	11/034,418	01/12/05	RF Field Heated Diodes for Providing Thermally Assisted Switching of Magnetic Memory Elements	HPDC 01/12/05 Samsung 07/26/07	016180 019614	0951 0001	5649-2250